



ILC Polarized Electron Source

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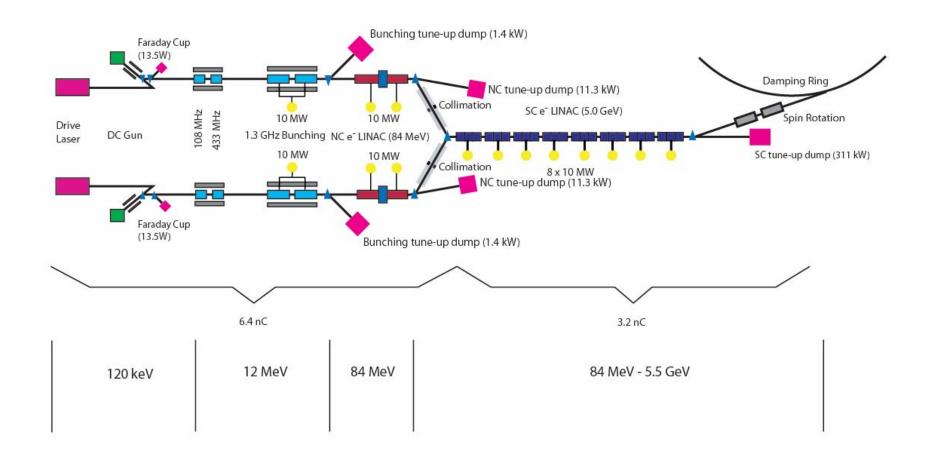


- Layout based on ILC source requirements
- Beam line optics design
- Current R&D Program
 - Photocathode R&D
 - Laser development program



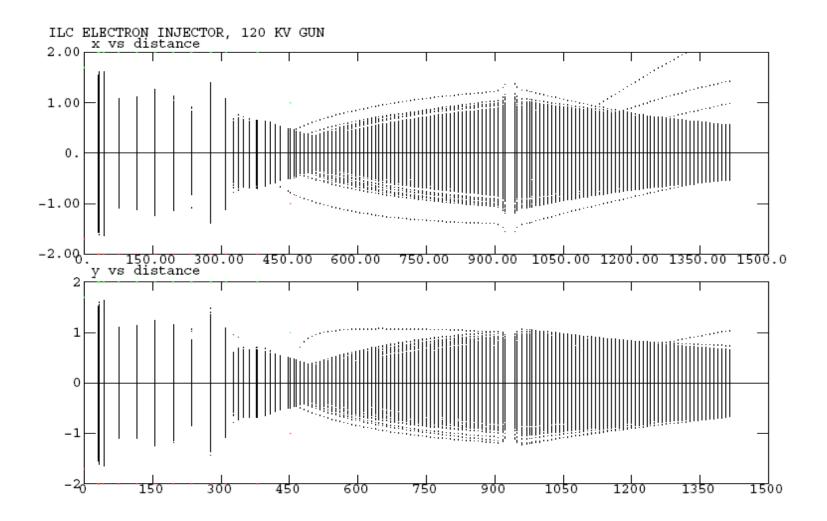


Polarized Electron Source Schematic Layout





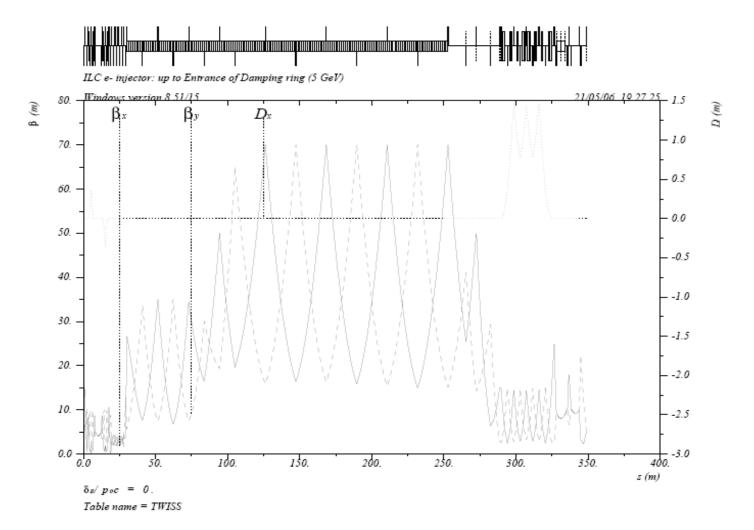
Beam Line Optics Design : 120 keV to 84 MeV





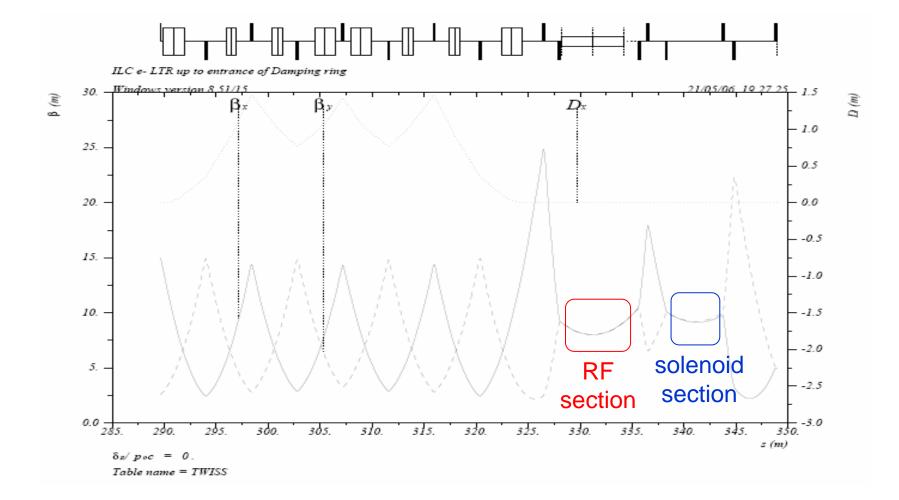


Beam Line Optics Design : Electron Booster Linac (5 GeV)





Beam Line Optics Design : Linac to DR Transfer Spin Rotation and Energy Compression

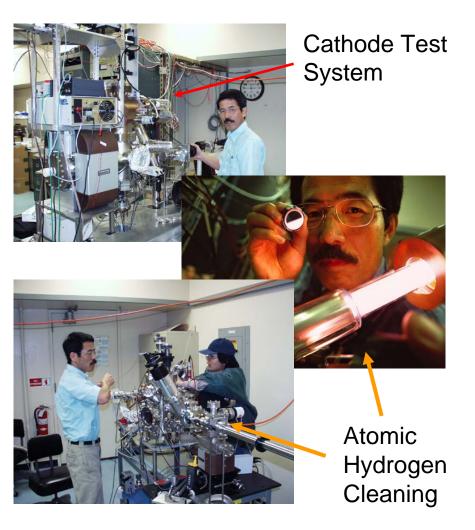






Photocathode R&D program at SLAC

- SLAC has a long history of cathode development for polarized electron beams
- Collaboration with industry using DOE's SBIR program – currently 'development of gridded photocathodes for improved QE and Polarization' with Saxet Inc.
- Collaboration with universities through 'Polarized Photocathodes Research Collaboration – PPRC'
- Participation of many SLAC support groups, e.g. Surface and Materials Science Group, Vacuum Group





at Stanford Linear Accelerator Center

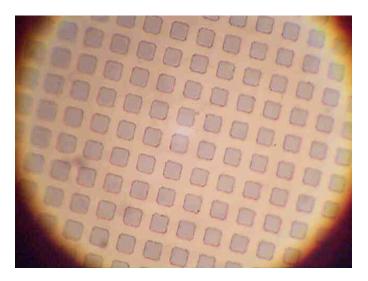


Photocathode R&D: Improve Quantum Efficiency and Polarization

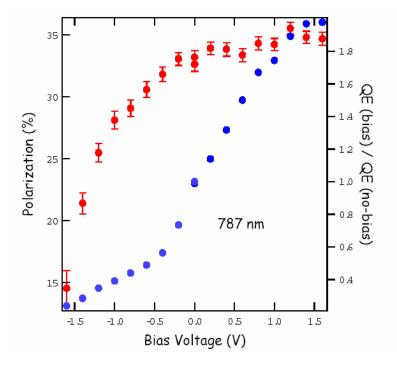
Example : Biased photocathodes

Positive bias

- $\succ \quad \text{Larger NEA} \rightarrow \text{higher QE}$
- ➤ Faster electrons → higher polarization Bias voltage supplied by photolithographically deposited tungsten grid.



Thin unstrained GaAs







Injector Test Facility – Integrated Photoinjector Test Lab

Existing Facilities:

- Laser Development Lab
- Gun Development Lab
- Cathode Test Lab
- High Voltage Test Facility

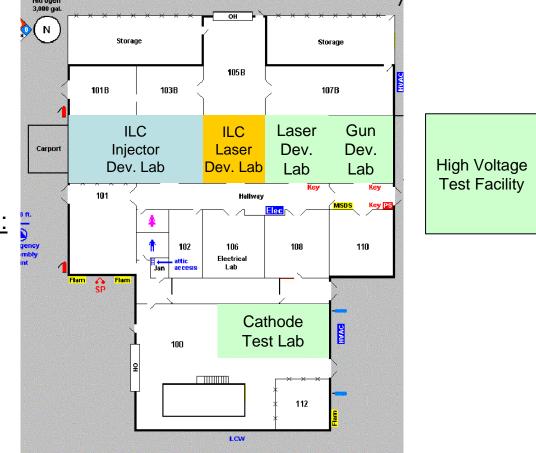
Facilities in Preparation (this FY):

- ILC Laser Development Lab

Future Facilities:

- ILC Injector Development Lab

Upgraded Injector Test Facility







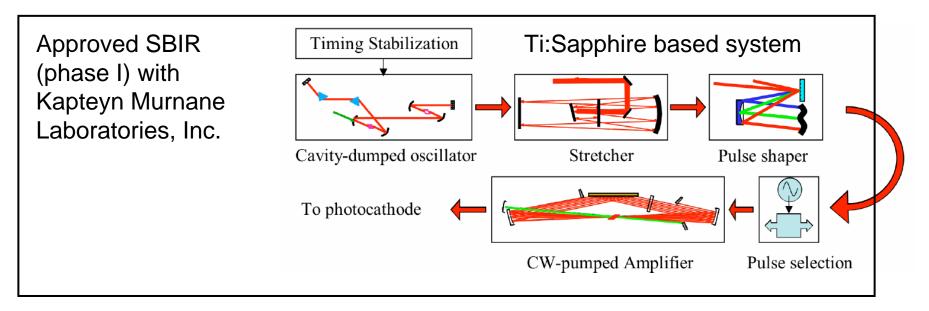
Proposed Laser System

Requirements based on ILC parameters and photocathodes for polarized electrons:

Challenge: Pulse train amplification at 3 MHz (6 MHz for upgraded ILC) using Ti:Sapphire

 \rightarrow no commercial or demonstrated solution \rightarrow R&D REQUIRED

Wavelength:	800 nm \rightarrow matching of GaAs bandgap
Energy:	~ 5 micro Joules
Pulse format:	2 ns pulse at 3 MHz, 1 ms burst







Outlook for FY 07

- Laser System Development and integration into Injector Test Facility
 - Laser transport to ITF Gun → generate ILC beam, demonstrate polarized electron pulse train generation with GaAs cathodes
- Continue Photocathode R&D
 - Further improvement of polarization and QE
 - Upgrade lab equipment next generation cathode test system
 - New photocathode material
- ➢ Gun R&D
 - new electrodes for polarized gun
 - Improved HV design